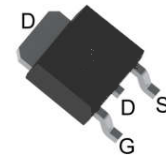
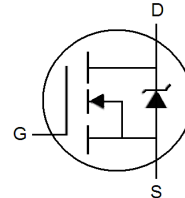


N-CHANNEL Power MOSFET
FEATURES

- V_{DS} :650VMax., I_D : 7A Max.
- $R_{DS(ON)}$:1.3 Ω (max.)@ $V_{GS}=10V, I_D=1A$
- High density cell design for ultra low on-resistance
- Fully characterized avalanche voltage and current


TO-252

EQUIVALENT CIRCUIT
MECHANICAL DATA

- Case: TO-252
- Case material: Molded Plastic. UL flammability 94V-0
- Weight:0.33grams(approximate)
- Marking:D7N65

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

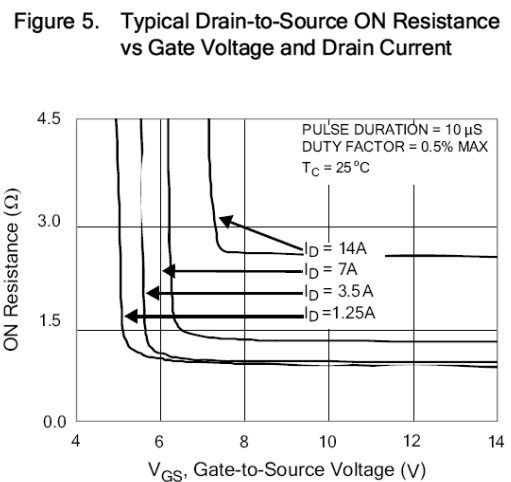
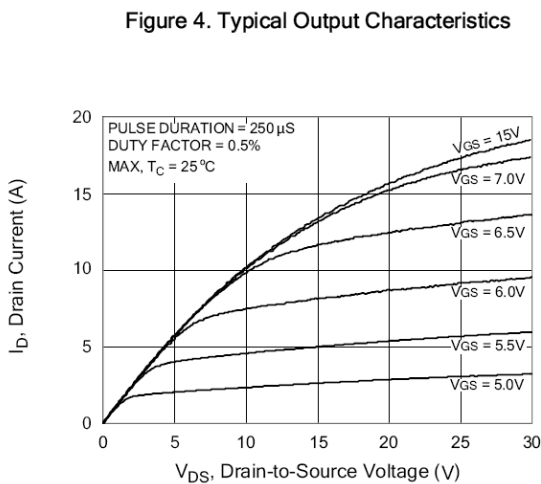
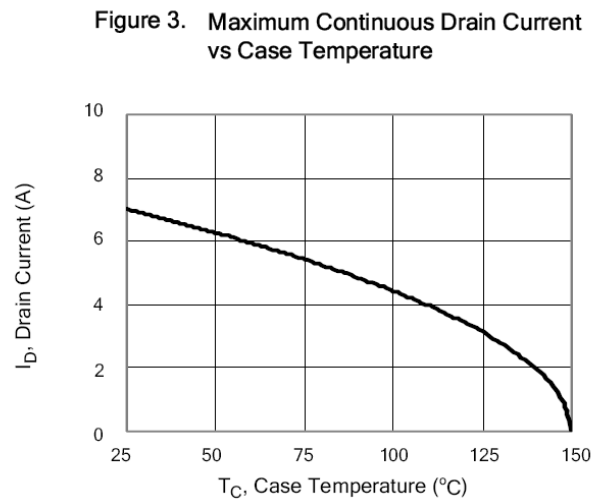
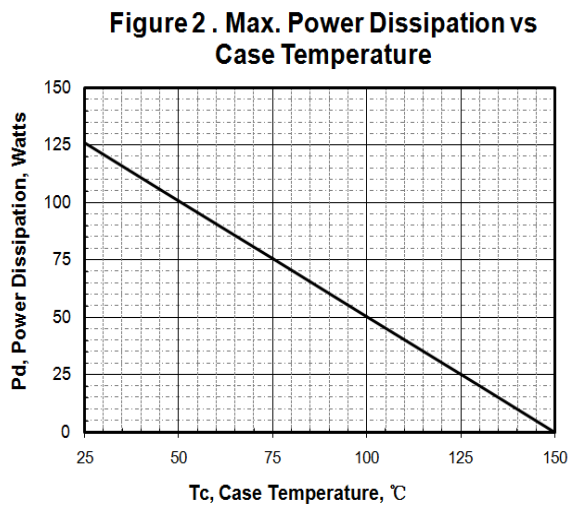
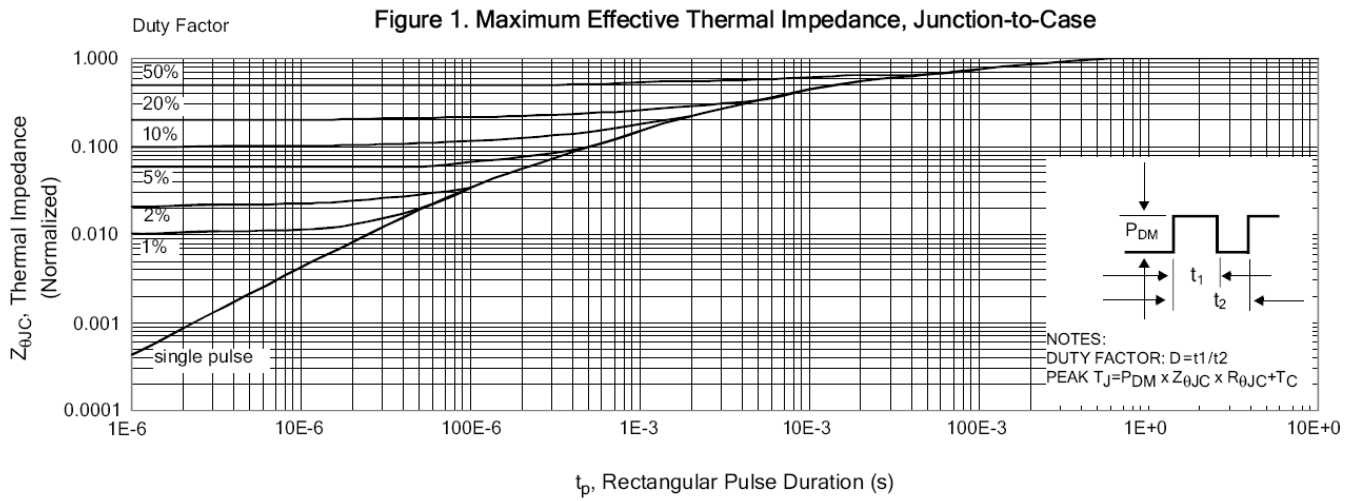
Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	650	V
Gate-source voltage	V_{GS}	± 30	V
Continuous drain current, $V_{GS}=10V$	I_D	7	A
Pulsed drain current (Note 1)	I_{DM}	28	A
Power dissipation	P_D	27.2	W
Thermal resistance from junction to ambient	$R_{\theta JA}$	100	$^\circ\text{C/W}$
Operating junction and storage temperature	T_J, T_{STG}	-55~+150	$^\circ\text{C}$
Single Pulsed Avalanche Energy (note 1)	E_{AS}	550	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10s)	T_L	260	$^\circ\text{C}$

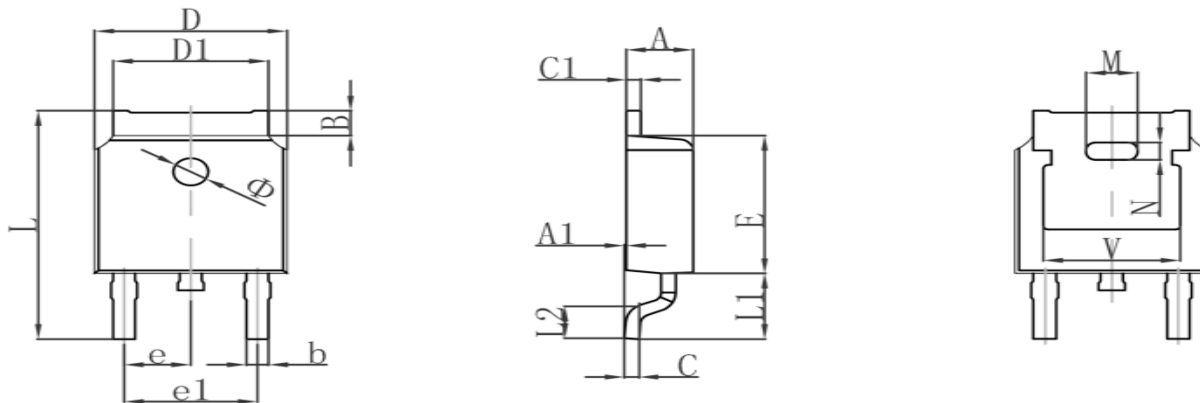
Note: 1. E_{AS} condition: $V_{DD}=20V, L=0.5mH, R_G=25\Omega$, Starting $T_J = 25^\circ\text{C}$

N-CHANNEL Power MOSFET
ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

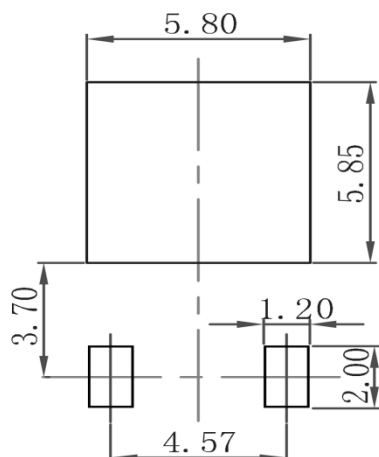
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	650	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 650V, V_{GS} = 0V, T_J = 25^\circ C$	--	--	100	nA
I_{GSS}	Gate-Source Leakage	$V_{GS} = \pm 30V$	--	--	± 100	nA
$V_{GS(th)}$	Gate-Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0	--	4.0	V
$R_{DS(on)}$	Drain-Source On-Resistance (Note3)	$V_{GS} = 10V, I_D = 1A$	--	1.08	1.3	Ω
C_{iss}	Input Capacitance	$V_{GS} = 0V,$ $V_{DS} = 25V, f = 1.0MHz$	--	1120	--	pF
C_{oss}	Output Capacitance		--	90	--	
C_{rss}	Reverse Transfer Capacitance		--	10	--	
Q_g	Total Gate Charge	$V_{DD} = 325V, I_D = 7A,$ $V_{GS} = 10V$	--	20	--	nC
Q_{gs}	Gate-Source Charge		--	5	--	
Q_{gd}	Gate-Drain Charge		--	5	--	
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 325V, I_D = 7A,$ $R_G = 4.7\Omega$	--	12	--	ns
t_r	Turn-on Rise Time		--	12	--	
$t_{d(off)}$	Turn-off Delay Time		--	18	--	
t_f	Turn-off Fall Time		--	10	--	
I_S	Continuous Body Diode Current	$T_C = 25^\circ C$	--	--	7	A
I_{SM}	Pulsed Diode Forward Current		--	--	28	
V_{SD}	Body Diode Voltage	$T_J = 25^\circ C, I_{SD} = 1.0A, V_{GS} = 0V$	--	--	0.9	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0V, I_S = 7.0A,$ $di_f/dt = 100A/\mu s$	--	350	--	ns
Q_{rr}	Reverse Recovery Charge		--	1.1	--	μC

**N-CHANNEL Power MOSFET
TYPICAL CHARACTERISTICS**



N-CHANNEL Power MOSFET
TO-252 PACKAGE OUTLINE DIMENSIONS


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.380	0.087	0.094
A1	0.000	0.100	0.000	0.004
B	0.800	1.400	0.031	0.055
b	0.710	0.810	0.028	0.032
c	0.460	0.560	0.018	0.022
c1	0.460	0.560	0.018	0.022
D	6.500	6.700	0.256	0.264
D1	5.130	5.460	0.202	0.215
E	6.000	6.200	0.236	0.244
e	2.286TYP		0.090TYP	
e1	4.327	4.727	0.170	0.186
M	1.778REF		0.070REF	
N	0.762REF		0.018REF	
L	9.800	10.400	0.386	0.409
L1	2.9REF		0.114REF	
L2	1.400	1.700	0.055	0.067
V	4.830REF		0.190REF	
Φ	1.100	1.300	0.043	0.051

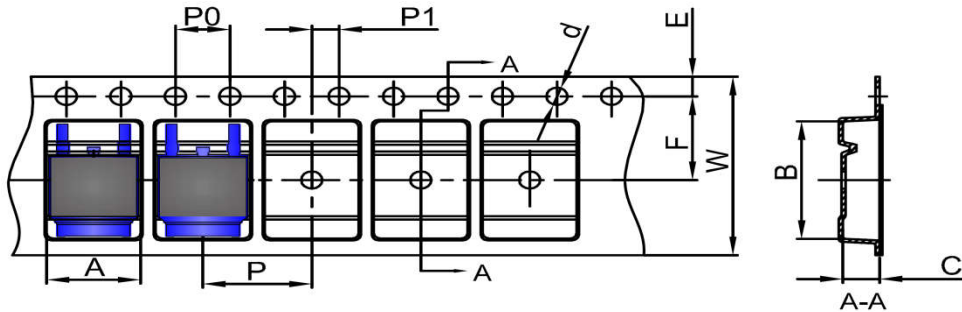
TO-252 SUGGESTED PAD LAYOUT

Note:

1. Controlling dimension: in millimeters
2. General tolerance: $\pm 0.05\text{mm}$
3. The pad layout is for reference purposes only

N-CHANNEL Power MOSFET

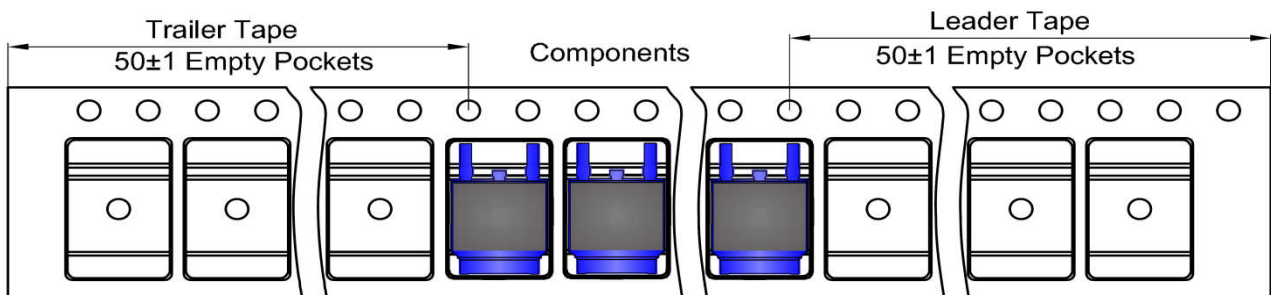
TO-252 TAPE AND REEL

TO-252 Embossed Carrier Tape

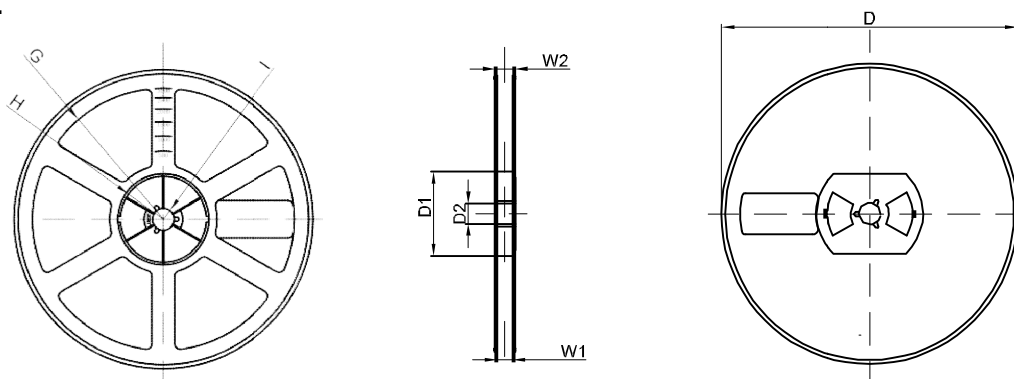


DIMENSIONS ARE IN MILLIMETER										
TYPE	A	B	C	d	E	F	P0	P	P1	W
TO-252	6.90	10.50	2.70	Ø1.55	1.75	7.50	4.00	8.00	2.00	16.00
TOLERANCE	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1

TO-252 Tape Leader and Trailer



TO-252 REEL



DIMENSIONS ARE IN MILLIMETER								
REEL OPTION	D	D1	D2	G	H	I	W1	W2
13" DIA	Ø330.00	100.00	Φ21.00	R151.00	R56.00	R6.50	16.40	21.00
TOLERANCE	±2	±1	±1	±1	±1	±1	±1	±1